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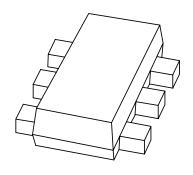
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PBSS3515VS15 V low V_{CE(sat)} PNP double transistor

Product data sheet Supersedes data of 2001 Nov 07 2004 Dec 23



15 V low V_{CE(sat)} PNP double transistor

PBSS3515VS

FEATURES

- 300 mW total power dissipation
- Very small 1.6 × 1.2 mm ultra thin package
- · Self alignment during soldering due to straight leads
- Low collector-emitter saturation voltage
- · High current capability
- Improved thermal behaviour due to flat leads
- Replaces two SC75/SC89 packaged low V_{CEsat} transistors on same PCB area
- · Reduces required PCB area
- · Reduced pick and place costs.

APPLICATIONS

- · General purpose switching and muting
- · Low frequency driver circuits
- · LCD backlighting
- Audio frequency general purpose amplifier applications
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

PNP low V_{CEsat} double transistor in a SOT666 plastic package.

NPN complement: PBSS2515VS.

MARKING

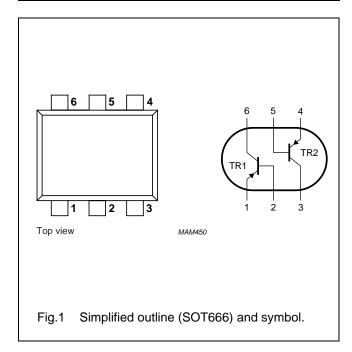
TYPE NUMBER	MARKING CODE
PBSS3515VS	35

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	-15	V
I _{CM}	peak collector current	-1	Α
R _{CEsat}	equivalent on-resistance	<500	mΩ

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



ORDERING INFORMATION

TYPE NUMBER	PACKAGE				
TIPE NOWIDER	NAME	NAME DESCRIPTION VERSION			
PBSS3515VS	_	plastic surface mounted package; 6 leads	SOT666		

15 V low $V_{\text{CE(sat)}}$ PNP double transistor

PBSS3515VS

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transis	Per transistor unless otherwise specified					
V _{CBO}	collector-base voltage	open emitter	_	-15	V	
V_{CEO}	collector-emitter voltage	open base	_	-15	V	
V _{EBO}	emitter-base voltage	open collector	_	-6	V	
I _C	collector current (DC)		_	-500	mA	
I _{CM}	peak collector current		_	-1	Α	
I _{BM}	peak base current		_	-100	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW	
T _{stg}	storage temperature		-65	+150	°C	
T _j	junction temperature		_	150	°C	
T _{amb}	operating ambient temperature		-65	+150	°C	
Per device	Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	300	mW	

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering method is reflow soldering.

15 V low $V_{\text{CE(sat)}}$ PNP double transistor

PBSS3515VS

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Per transis	Per transistor unless otherwise specified						
I _{CBO}	collector-base cut-off current	$V_{CB} = -15 \text{ V}; I_E = 0 \text{ A}$	_	_	-100	nA	
		$V_{CB} = -15 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ	
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V; } I_{C} = 0 \text{ A}$	_	_	-100	nA	
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = -10 \text{ mA}$	200	_	_		
		$V_{CE} = -2 \text{ V; } I_{C} = -100 \text{ mA; note 1}$	150	-	-		
		$V_{CE} = -2 \text{ V}; I_{C} = -500 \text{ mA}; \text{ note 1}$	90	_	_		
V _{CEsat}	collector-emitter saturation	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	_	-25	mV	
	voltage	$I_C = -200 \text{ mA}; I_B = -10 \text{ mA}$	-	-	-150	mV	
		$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}; \text{ note 1}$	-	_	-250	mV	
R _{CEsat}	equivalent on-resistance	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}; \text{ note 1}$	-	300	<500	mΩ	
V _{BEsat}	base-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}; \text{ note 1}$	-	-	-1.1	V	
V_{BE}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -100 \text{ mA}; \text{ note 1}$	-	_	-0.9	V	
f _T	transition frequency	$I_C = -100 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	100	280	_	MHz	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0 \text{ A}; f = 1 \text{ MHz}$	-	_	10	pF	

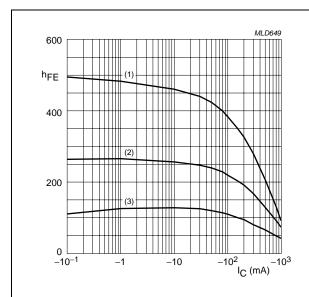
Note

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

2004 Dec 23

15 V low $V_{\text{CE(sat)}}$ PNP double transistor

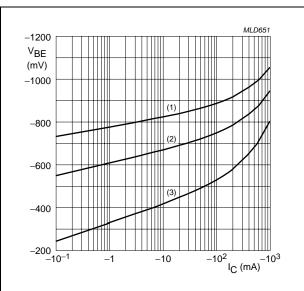
PBSS3515VS



 $V_{CE} = -2 V$.

- (1) T_{amb} = 150 °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

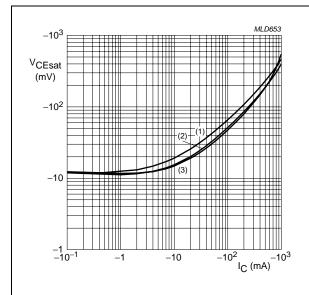
Fig.2 DC current gain as a function of collector current; typical values.



 $V_{CE} = -2 \text{ V}.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

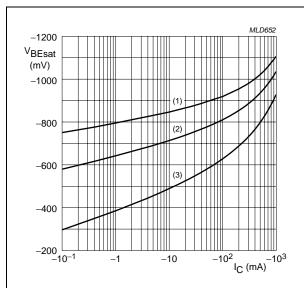
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



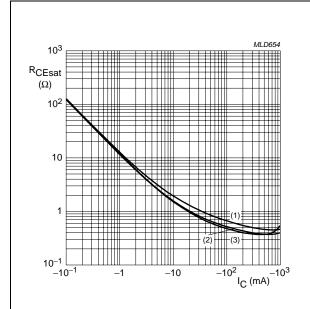
 $I_{\rm C}/I_{\rm B} = 20.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

15 V low $V_{\text{CE(sat)}}$ PNP double transistor

PBSS3515VS



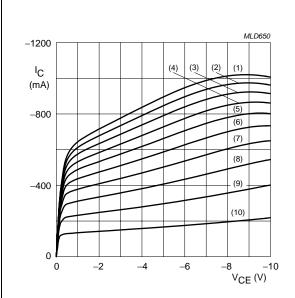
 $I_{C}/I_{B}=20.$

(1) $T_{amb} = 150 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.6 Equivalent on-resistance as a function of collector current; typical values.



 $T_{amb} = 25 \, ^{\circ}C.$

(1) $I_B = -7 \text{ mA}$.

(6) $I_B = -3.5 \text{ mA}.$

(2) $I_B = -6.3 \text{ mA}.$

(7) $I_B = -2.8 \text{ mA}.$

(3) $I_B = -5.6 \text{ mA}.$

(8) $I_B = -2.1 \text{ mA}.$

(4) $I_B = -4.9 \text{ mA}.$

(9) $I_B = -1.4 \text{ mA}.$

(5) $I_B = -4.2 \text{ mA}.$

(10) $I_B = -0.7 \text{ mA}$.

Fig.7 Collector current as a function of collector-emitter voltage; typical values.

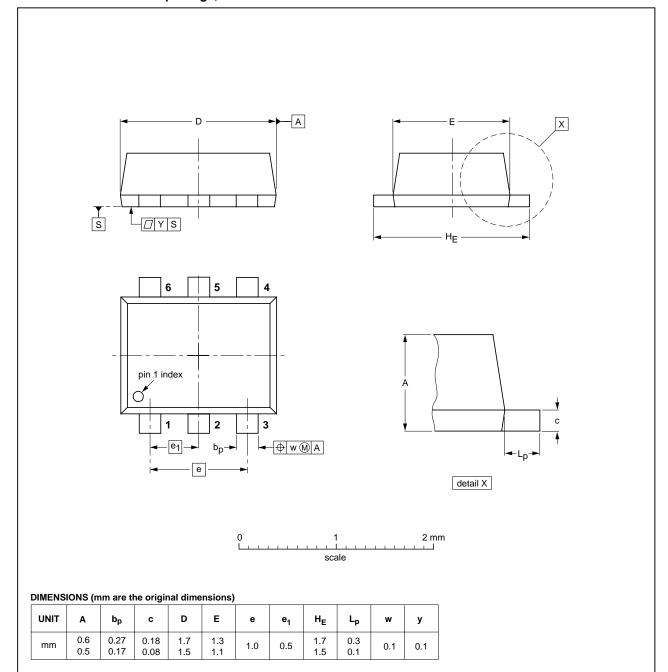
15 V low $V_{\text{CE(sat)}}$ PNP double transistor

PBSS3515VS

PACKAGE OUTLINE

Plastic surface-mounted package; 6 leads

SOT666



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT666						-04-11-08- 06-03-16

15 V low V_{CE(sat)} PNP double transistor

PBSS3515VS

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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